







Radiation hardness of fully depleted CMOS Monolithic Active Pixel Sensors

Tobias Bus, Benjamin Linnik, Michael Deveaux

MAPS – Monolithic Active Pixel Sensors





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Effects of non-ionizing radiation





Trapping & recombination of signal electrons

Leakage current → higher noise Cooling decreases this effect

Depleting the sensor allows to accelerate the charge collection. => More radiation tolerance.

Pipper – 2: A fully depleted HR-MAPS



ssue:

Standard CMOS restricted to few volts => Too few for full depletion.

Analysis:

Restriction due to transistor gates. Diodes and metal lines tolerate higher voltages.

Approach:

Use AC-couping to separate vulnerable transistors from HV on diode.

 \Rightarrow Depletion voltage up to 40V possible.

Apply to 22x22 μ m² pixels.



Standard sensor – Test results





Standard sensor – Only few hits from depleted volume. Other hits: Reduced amplitude (charge sharing).



Pipper – 2 – Test results



Hits mostly in depleted volume peak. No modification for >20V => indicator for full depletion

VIIt keine zeit dafür?





Test with ⁹⁰Sr beta rays





S/N (Sr-90) >15 ⇔ typically > 99% MIP - efficiency

T = -55° C	Signal MPV (e)	Avg. noise (e)	S/N	
10 ¹³ n _{eq} /cm ²	1290	23.19	55.6	
$5 \cdot 10^{14} n_{eq}^{2}/cm^{2}$	860	27.48	31.3	

Summary and conclusion



A CMOS sensor allowing for 40V depletion voltage in Tower/Jazz 0.18µm has been built and tested.

Results suggest full depletion.

Laboratory tests suggest tolerance to >5 x $10^{14} n_{eq}/cm^2$. (Remaining S/N>30 if cooled).

